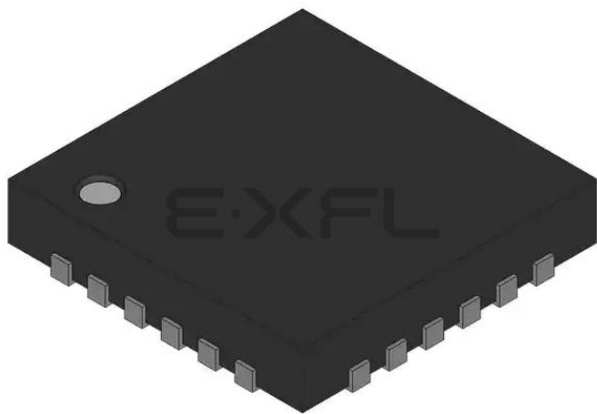




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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 12x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VFQFN Exposed Pad
Supplier Device Package	24-QFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl05z16vfk4

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to www.freescale.com and perform a part number search for the following device numbers: PKL05 and MKL05

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	- M = Fully qualified, general market flow - P = Prequalification
KL##	Kinetis family	KL05
A	Key attribute	Z = Cortex-M0+
FFF	Program flash memory size	8 = 8 KB 16 = 16 KB 32 = 32 KB
R	Silicon revision	(Blank) = Main - A = Revision after main

Table continues on the next page...

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V _{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I _{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V _{DD}	Digital supply voltage	-0.3	3.8	V
I _{DD}	Digital supply current	—	120	mA
V _{DIO}	Digital pin input voltage (except RESET)	-0.3	V _{DD} + 0.3	V
V _{AIO}	Analog pins ¹ and RESET pin input voltage	-0.3	V _{DD} + 0.3	V
I _D	Instantaneous maximum current single pin limit (applies to all port pins)	-25	25	mA
V _{DDA}	Analog supply voltage	V _{DD} - 0.3	V _{DD} + 0.3	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{ICIO}	I/O pin DC injection current — single pin $V_{IN} < V_{SS}-0.3V$ (Negative current injection) $V_{IN} > V_{DD}+0.3V$ (Positive current injection)	-3 —	— +3	mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} ($=V_{SS}-0.3V$) and V_{IN} is less than $V_{AIO_MAX}(=V_{DD}+0.3V)$ is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V_{LVW1H}	Low-voltage warning thresholds — high range Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	1
V_{LVW2H}	Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V_{LVW3H}	Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V_{LVW4H}	Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V_{LVW1L}	Low-voltage warning thresholds — low range Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	1
V_{LVW2L}	Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V_{LVW3L}	Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	

Table continues on the next page...

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash - at 3.0 V - at 25 °C - at 125 °C	— —	5.6 6	6.8 7.2	mA mA	2, 3
I _{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	—	3.0	4.2	mA	2
I _{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	—	2.4	3.36	mA	2
I _{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus at 3.0 V	—	2.25	3.38	mA	2
I _{DD_VLPRCO}	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash at 3.0 V	—	182	522	μA	4
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash at 3.0 V	—	213.33	577.8	μA	4
I _{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash at 3.0 V	—	242.8	631.8	μA	3, 4
I _{DD_VLPW}	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled at 3.0 V	—	106.1	399.42	μA	4

Table continues on the next page...

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I _{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 0) - at 3.0 V - at 25 °C - at 50 °C - at 70 °C - at 85 °C - at 105 °C				nA	
		—	449.6	959.2		
		—	1200	12155.08		
		—	2900	15323.29		
		—	5900	16384.55		
		—	14800	26773.45		
I _{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 1) - at 3.0 V - at 25 °C - at 50 °C - at 70 °C - at 85 °C - at 105 °C				nA	5
		—	221.7	894.24		
		—	1000	3784.55		
		—	2600	12018.39		
		—	5600	18722.23		
		—	14400	24665.06		

1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
2. MCG configured for FEI mode.
3. Incremental current consumption from peripheral activity is not included.
4. MCG configured for BLPI mode.
5. No brownout

Table 6. Low power mode peripheral adders — typical value

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I _{IREFSTEN4MHz}	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.	56	56	56	56	56	56	μA
I _{IREFSTEN32KHz}	32 kHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 32 kHz IRC enabled.	52	52	52	52	52	52	μA
I _{EREFSTEN4MHz}	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	228	237	245	251	258	uA

Table continues on the next page...

5.3 Switching specifications

5.3.1 Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f _{SYS}	System and core clock	—	48	MHz	
f _{BUS}	Bus clock	—	24	MHz	
f _{FLASH}	Flash clock	—	24	MHz	
f _{LPTMR}	LPTMR clock	—	24	MHz	
VLPR mode ¹					
f _{SYS}	System and core clock	—	4	MHz	
f _{BUS}	Bus clock	—	1	MHz	
f _{FLASH}	Flash clock	—	1	MHz	
f _{LPTMR}	LPTMR clock	—	24	MHz	
f _{ERCLK}	External reference clock	—	16	MHz	
f _{LPTMR_pin}	LPTMR clock	—	24	MHz	
f _{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
f _{osc_hi_2}	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	—	16	MHz	
f _{TPM}	TPM asynchronous clock	—	8	MHz	
f _{UART0}	UART0 asynchronous clock	—	8	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General Switching Specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and I²C signals.

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
	GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
	Port rise and fall time	—	36	ns	3

General

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 8. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	−40	125	°C
T_A	Ambient temperature	−40	105	°C

5.4.2 Thermal attributes

Table 9. Thermal attributes

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	82	88	97	110	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	58	59	34	42	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	70	74	81	92	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	52	52	28	36	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	13	18	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	27	26	2.3	3.7	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	8	8	8	10	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions — Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions — Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions — Junction-to-Board*.

Table 12. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{pp}^5	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. $V_{DD}=3.3$ V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x, C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

6.3.2.2 Oscillator frequency specifications

Table 13. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc_hi_1}$	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc_hi_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	—	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	—	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors

Table 16. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 17. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	—	years	
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	—	years	
n _{nvmcycp}	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40^{\circ}\text{C} \leq T_j \leq 125^{\circ}\text{C}$.

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

6.6.1.1 12-bit ADC operating conditions**Table 18. 12-bit ADC operating conditions**

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 8-/10-/12-bit modes	—	4	5	pF	
R_{ADIN}	Input resistance		—	2	5	k Ω	
R_{AS}	Analog source resistance	12-bit modes $f_{ADCK} < 4$ MHz	—	—	5	k Ω	4
f_{ADCK}	ADC conversion clock frequency	$\leq$ 12-bit mode	1.0	—	18.0	MHz	5
C_{rate}	ADC conversion rate	$\leq$ 12 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

1. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25 °C, $f_{ADCK} = 1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA} , and V_{REFL} is internally tied to V_{SSA} .
4. This resistance is external to MCU. The analog source resistance must be kept as low as possible to achieve the best results. The results in this data sheet were derived from a system which has $< 8 \Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
5. To use the maximum ADC conversion clock frequency, the ADHSC bit must be set and the ADLPC bit must be clear.
6. For guidelines and examples of conversion rate calculation, download the [ADC calculator tool](#)

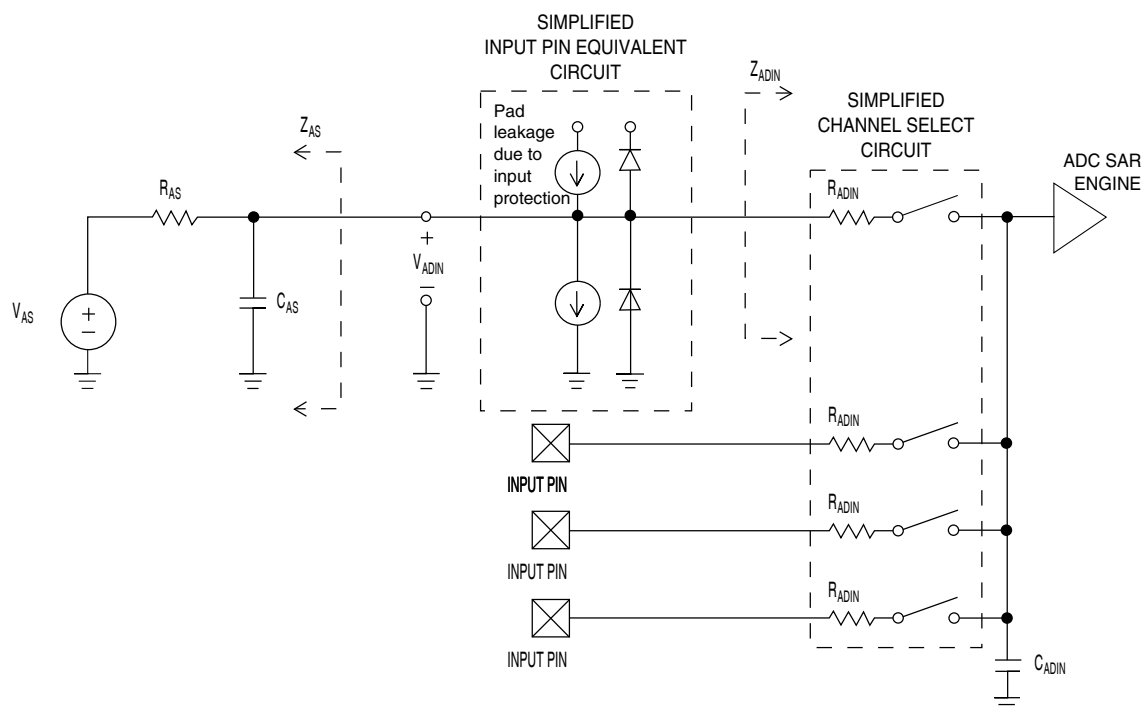


Figure 6. ADC input impedance equivalency diagram

6.6.1.2 12-bit ADC electrical characteristics

Table 19. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB ⁴	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB ⁴	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB ⁴	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	-4 -1.4	-5.4 -1.8	LSB ⁴	$V_{ADIN} = V_{DDA}$ 5

Table continues on the next page...

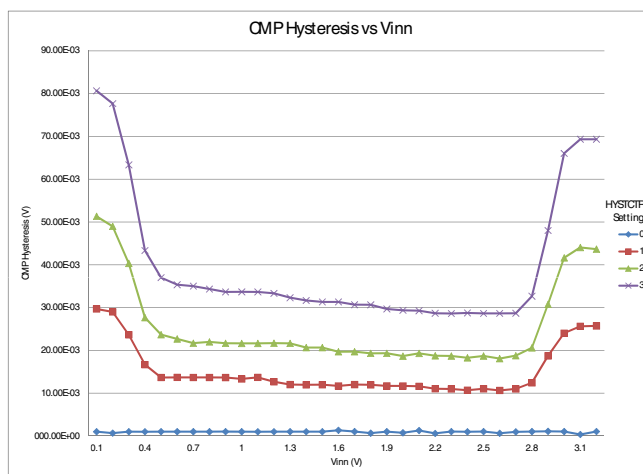


Figure 8. Typical hysteresis vs. Vin level ($V_{DD} = 3.3$ V, PMODE = 0)

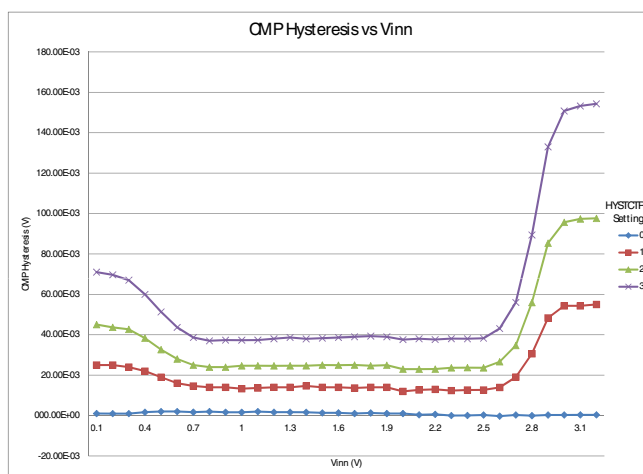


Figure 9. Typical hysteresis vs. Vin level ($V_{DD} = 3.3$ V, PMODE = 1)

6.6.3 12-bit DAC electrical characteristics

6.6.3.1 12-bit DAC operating requirements

Table 21. 12-bit DAC operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage		3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
T_A	Temperature	Operating temperature range of the device		°C	
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or the voltage output of the VREF module (VREF_OUT)
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC

6.6.3.2 12-bit DAC operating behaviors

Table 22. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	250	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	900	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	$V_{DACR} - 100$	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	± 8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2 V$	—	—	± 1	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = V_{REF_OUT}$	—	—	± 1	LSB	4
V_{OFFSET}	Offset error	—	± 0.4	± 0.8	%FSR	5
E_G	Gain error	—	± 0.1	± 0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4 V$	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	$\mu V/C$	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance load = 3 k Ω	—	—	250	Ω	
SR	Slew rate -80h → F7Fh → 80h - High power (SP_{HP}) - Low power (SP_{LP})	1.2 0.05	1.7 0.12	— —	V/ μs	
BW	3dB bandwidth - High power (SP_{HP}) - Low power (SP_{LP})	550 40	— —	— —	kHz	

- Settling within ± 1 LSB
- The INL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
- The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
- The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV with $V_{DDA} > 2.4 V$
- Calculated by a best fit curve from $V_{SS} + 100$ mV to $V_{DACR} - 100$ mV
- $V_{DDA} = 3.0 V$, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

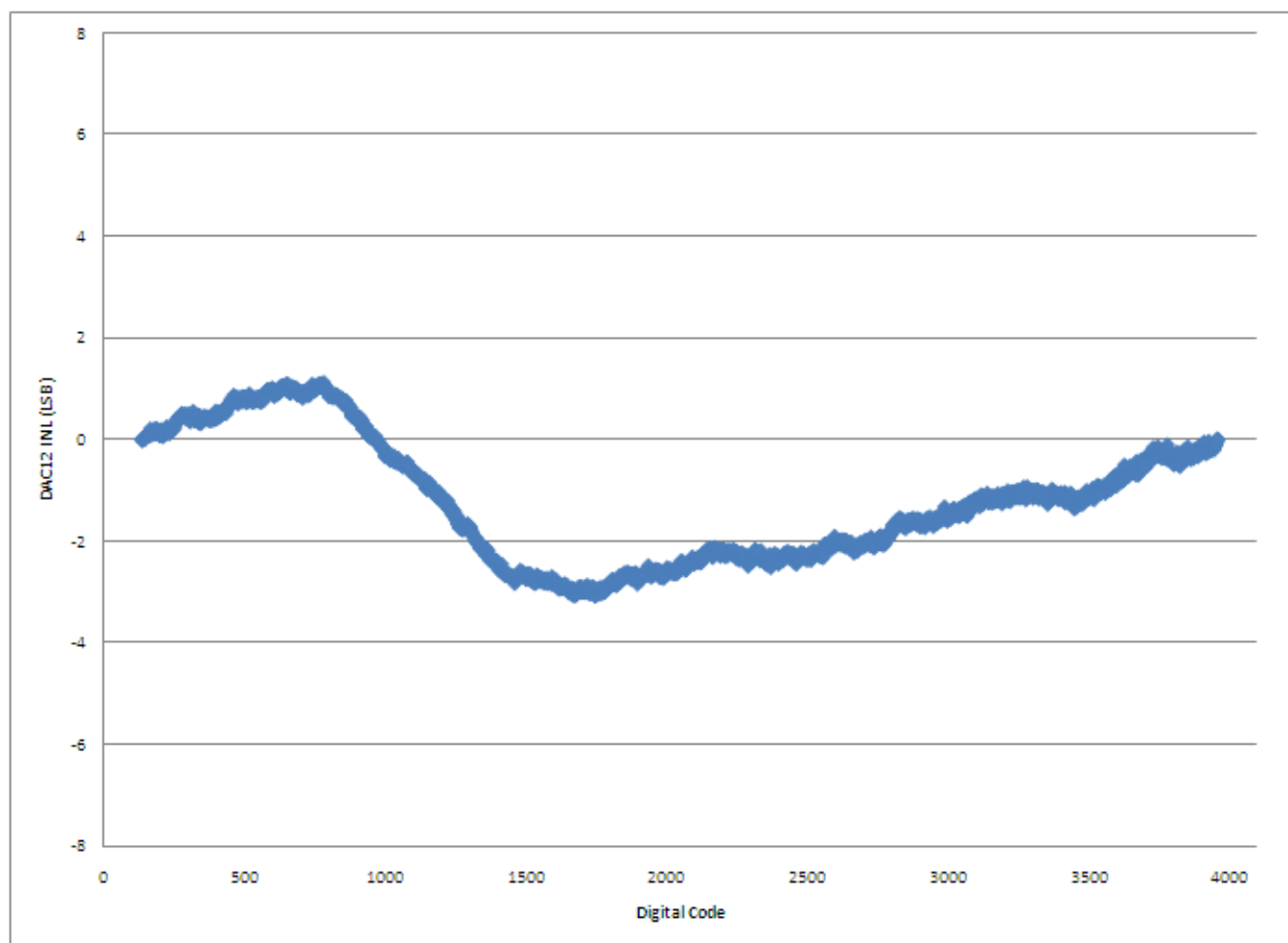


Figure 10. Typical INL error vs. digital code

Table 25. SPI slave mode timing on slew rate disabled pads (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Note
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCCK edge)	—	22	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

Table 26. SPI slave mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCCK}	SPSCCK period	$4 \times t_{periph}$	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{periph} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0 f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

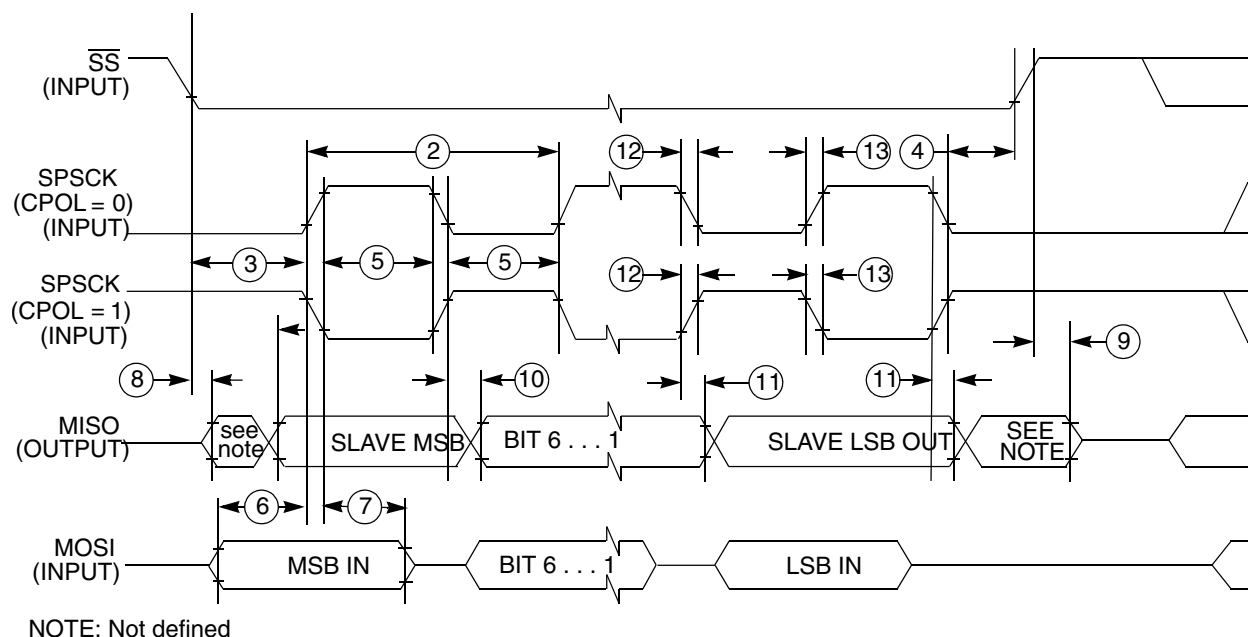


Figure 14. SPI slave mode timing (CPHA = 0)

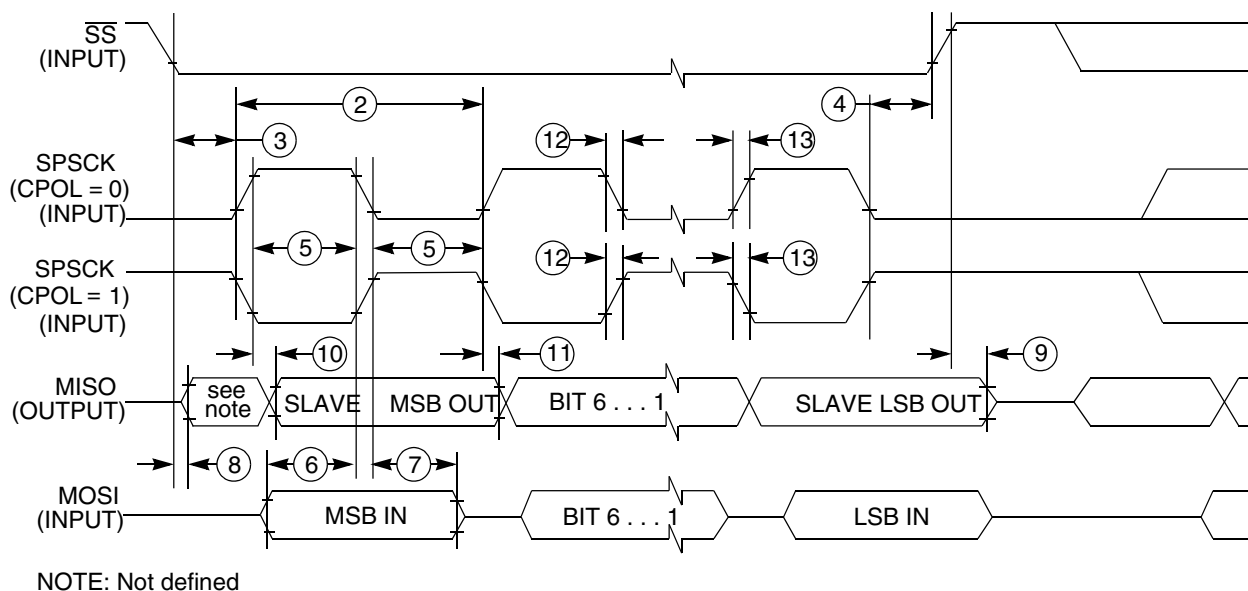


Figure 15. SPI slave mode timing (CPHA = 1)

6.8.2 I²C

See General switching specifications.

6.8.3 UART

See General switching specifications.

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 27. TSI electrical specifications

Symbol	Description	Min.	Type	Max	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	μA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	μA
TSI_EN	Power consumption in enable mode	—	100	—	μA
TSI_DIS	Power consumption in disable mode	—	1.2	—	μA
TSI_TEN	TSI analog enable time	—	66	—	μs
TSI_CREF	TSI reference capacitor	—	1.0	—	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	0.19	—	1.03	V

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to www.freescale.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
24-pin QFN	98ASA00474D
32-pin QFN	98ASA00473D
32-pin LQFP	98ASH70029A
48-pin LQFP	98ASH00962A

8 Pinout

8.1 KL05 signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
1	1	1	1	PTB6/ IRQ_2/ LPTMR0_ALT3	DISABLED	DISABLED	PTB6/ IRQ_2/ LPTMR0_ALT3	TPM0_CH3	TPM_CLKIN1
2	2	2	2	PTB7/ IRQ_3	DISABLED	DISABLED	PTB7/ IRQ_3	TPM0_CH2	
3	—	—	—	PTA14	DISABLED	DISABLED	PTA14		TPM_CLKIN0
4	—	—	—	PTA15	DISABLED	DISABLED	PTA15		CLKOUT
5	3	3	3	VDD	VDD	VDD			
6	4	4	3	VREFH	VREFH	VREFH			
7	5	5	4	VREFL	VREFL	VREFL			
8	6	6	4	VSS	VSS	VSS			
9	7	7	5	PTA3	EXTAL0	EXTAL0	PTA3	I2C0_SCL	I2C0_SDA
10	8	8	6	PTA4/ LLWU_P0	XTAL0	XTAL0	PTA4/ LLWU_P0	I2C0_SDA	I2C0_SCL
11	—	—	—	VSS	VSS	VSS			
12	—	—	—	PTB18	DISABLED	DISABLED	PTB18		
13	—	—	—	PTB19	DISABLED	DISABLED	PTB19		
14	9	9	7	PTA5/ LLWU_P1/ RTC_CLK_IN	DISABLED	DISABLED	PTA5/ LLWU_P1/ RTC_CLK_IN	TPM0_CH5	SPI0_SS_b
15	10	10	8	PTA6/ LLWU_P2	DISABLED	DISABLED	PTA6/ LLWU_P2	TPM0_CH4	SPI0_MISO
16	11	11	—	PTB8	ADC0_SE11	ADC0_SE11	PTB8	TPM0_CH3	
17	12	12	—	PTB9	ADC0_SE10	ADC0_SE10	PTB9	TPM0_CH2	
18	—	—	—	PTA16/ IRQ_4	DISABLED	DISABLED	PTA16/ IRQ_4		
19	—	—	—	PTA17/ IRQ_5	DISABLED	DISABLED	PTA17/ IRQ_5		
20	—	—	—	PTA18/ IRQ_6	DISABLED	DISABLED	PTA18/ IRQ_6		
21	13	13	9	PTB10	ADC0_SE9/ TSIO_IN7	ADC0_SE9/ TSIO_IN7	PTB10	TPM0_CH1	
22	14	14	10	PTB11	ADC0_SE8/ TSIO_IN6	ADC0_SE8/ TSIO_IN6	PTB11	TPM0_CH0	
23	15	15	11	PTA7/ IRQ_7/ LLWU_P3	ADC0_SE7/ TSIO_IN5	ADC0_SE7/ TSIO_IN5	PTA7/ IRQ_7/ LLWU_P3	SPI0_MISO	SPI0_MOSI
24	16	16	12	PTB0/ IRQ_8/ LLWU_P4	ADC0_SE6/ TSIO_IN4	ADC0_SE6/ TSIO_IN4	PTB0/ IRQ_8/ LLWU_P4	EXTRG_IN	SPI0_SCK

Pinout

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
25	17	17	13	PTB1/ IRQ_9	ADC0_SE5/ TSIO_IN3/ DAC0_OUT/ CMP0_IN3	ADC0_SE5/ TSIO_IN3/ DAC0_OUT/ CMP0_IN3	PTB1/ IRQ_9	UART0_TX	UART0_RX
26	18	18	14	PTB2/ IRQ_10/ LLWU_P5	ADC0_SE4/ TSIO_IN2	ADC0_SE4/ TSIO_IN2	PTB2/ IRQ_10/ LLWU_P5	UART0_RX	UART0_TX
27	19	19	15	PTA8	ADC0_SE3/ TSIO_IN1	ADC0_SE3/ TSIO_IN1	PTA8		
28	20	20	16	PTA9	ADC0_SE2/ TSIO_IN0	ADC0_SE2/ TSIO_IN0	PTA9		
29	—	—	—	PTB20	DISABLED	DISABLED	PTB20		
30	—	—	—	VSS	VSS	VSS			
31	—	—	—	VDD	VDD	VDD			
32	—	—	—	PTB14/ IRQ_11	DISABLED	DISABLED	PTB14/ IRQ_11	EXTRG_IN	
33	21	21	—	PTA10/ IRQ_12	DISABLED	TSIO_IN11	PTA10/ IRQ_12		
34	22	22	—	PTA11/ IRQ_13	DISABLED	TSIO_IN10	PTA11/ IRQ_13		
35	23	23	17	PTB3/ IRQ_14	DISABLED	DISABLED	PTB3/ IRQ_14	I2C0_SCL	UART0_TX
36	24	24	18	PTB4/ IRQ_15/ LLWU_P6	DISABLED	DISABLED	PTB4/ IRQ_15/ LLWU_P6	I2C0_SDA	UART0_RX
37	25	25	19	PTB5/ IRQ_16	NMI_b	ADC0_SE1/ CMP0_IN1	PTB5/ IRQ_16	TPM1_CH1	NMI_b
38	26	26	20	PTA12/ IRQ_17/ LPTMR0_ALT2	ADC0_SE0/ CMP0_IN0	ADC0_SE0/ CMP0_IN0	PTA12/ IRQ_17/ LPTMR0_ALT2	TPM1_CH0	TPM_CLKIN0
39	27	27	—	PTA13	TSIO_IN9	TSIO_IN9	PTA13		
40	28	28	—	PTB12	TSIO_IN8	TSIO_IN8	PTB12		
41	—	—	—	PTA19	DISABLED	DISABLED	PTA19		SPI0_SS_b
42	—	—	—	PTB15	DISABLED	DISABLED	PTB15	SPI0_MOSI	SPI0_MISO
43	—	—	—	PTB16	DISABLED	DISABLED	PTB16	SPI0_MISO	SPI0_MOSI
44	—	—	—	PTB17	DISABLED	DISABLED	PTB17	TPM_CLKIN1	SPI0_SCK
45	29	29	21	PTB13	ADC0_SE13	ADC0_SE13	PTB13	TPM1_CH1	RTC_CLKOUT
46	30	30	22	PTA0/ IRQ_0/ LLWU_P7	SWD_CLK	ADC0_SE12/ CMP0_IN2	PTA0/ IRQ_0/ LLWU_P7	TPM1_CH0	SWD_CLK
47	31	31	23	PTA1/ IRQ_1/ LPTMR0_ALT1	RESET_b	DISABLED	PTA1/ IRQ_1/ LPTMR0_ALT1	TPM_CLKIN0	RESET_b
48	32	32	24	PTA2	SWD_DIO	DISABLED	PTA2	CMP0_OUT	SWD_DIO

8.2 KL05 Pinouts

The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

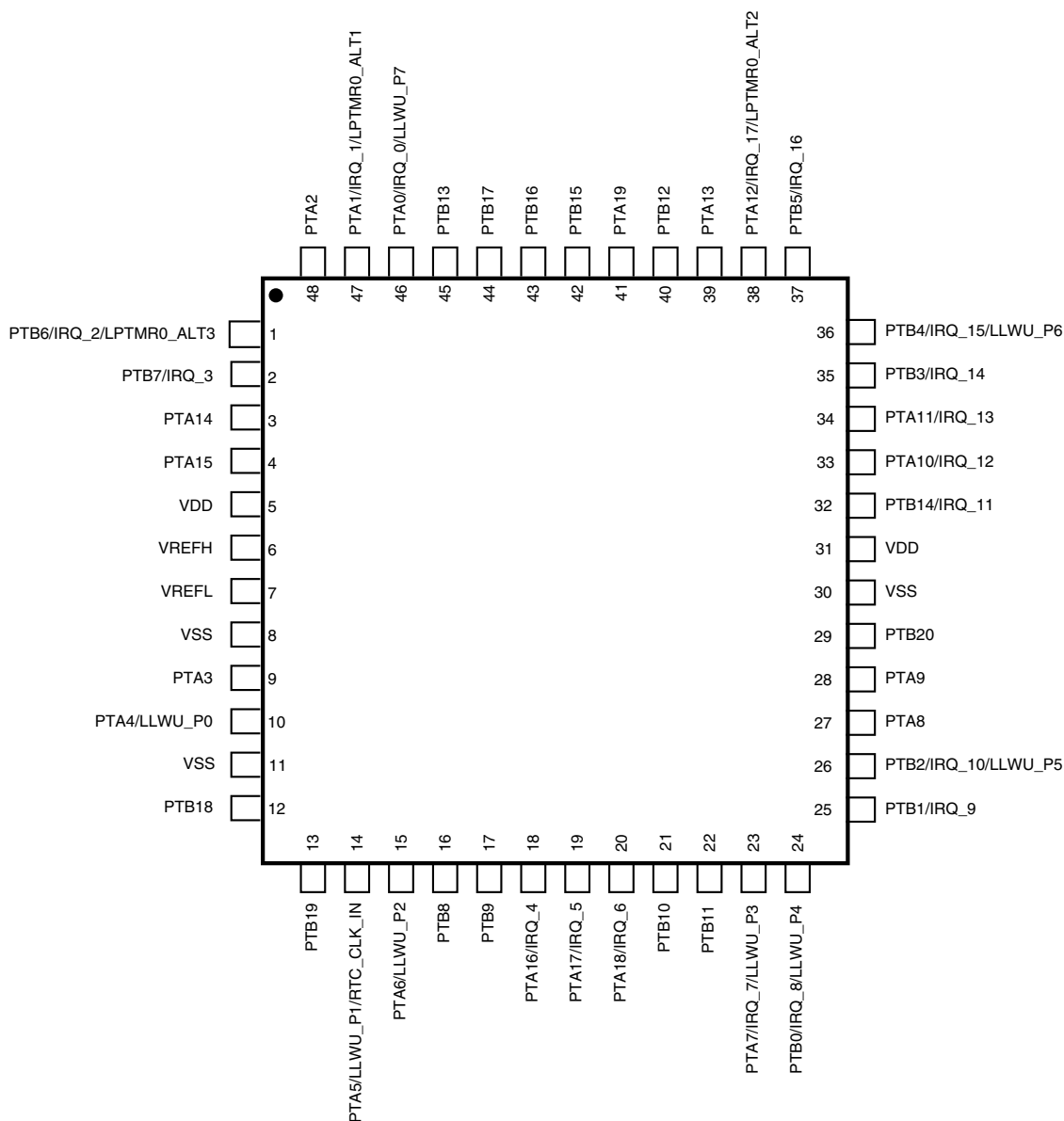


Figure 16. KL05 48-pin LQFP pinout diagram